

LED CHIP C1200-35

SPECIFICATION OF LED CHIP

C1200-35

[NIR]

1) Commodity Type and Physical Characteristics.

- 1. Material InGaAsP/InP(DDH)
- 2. Electrode Top Side P (anode) side : Au Alloy
Bottom Side N (cathode) side : Au Alloy
- 3. Electrode Pattern Fig.1
- 4. Chip Size Fig.2
- 5. Chip Thickness Fig.2
- 6. Emission Area Fig.2

2) Electro-Optical Characteristics

parameters	symbol	condition	min.	typ.	max.	unit
Forward Voltage	Vf	If=20mA		0.8	1.3	V
Reverse Current	Ir	Vr=3V			10	uA
Power Intensity	Po	If=20mA		0.6		mW
Peak Wavelength	λ P	If=20mA		1200		nm
Spectral Radiation Bandwidth	DI	If=20mA		100		nm
RiseTime	tr	If=20mA		10		ns
FallTime	tf	If=20mA		10		ns

‡ Die shall be mounted on TO=18 gold header without resin coated. (Ta=25°C)

[Unit: um]

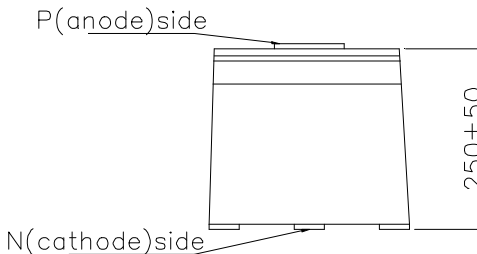
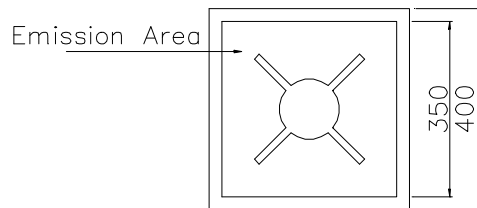
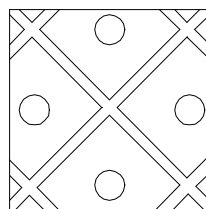
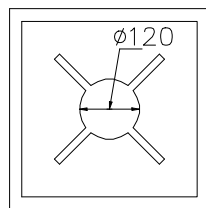


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area